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### Complete 5µs CMOS 10-Bit A/D Converter

#### **General Description**

The MAX173 is a complete, 10-bit linear analog-to-digital converter (ADC) that combines high speed, low power consumption, and an on-chip voltage reference. The conversion time is  $5\mu$ s. The buried zener reference provides low drift and low noise performance.

External component requirements are limited to only decoupling capacitors for the power supply and reference voltages. On-chip clock circuitry is also included which can either be driven from an external source, or in stand-alone applications, from a crystal.

The MAX173 uses a standard microprocessor interface architecture. Three-state data outputs are controlled by Read (RD) and Chip Select (CS) inputs. Data access and bus release times of 90ns and 75ns respectively ensure compatibility with most popular microprocessors without resorting to wait states.

#### **Applications**

Digital Signal Processing (DSP)

High Accuracy Process Control

High Speed Data Acquisition

Electro-Mechanical Systems

#### Features

- ♦ 12-Bit Resolution and 10-Bit Linearity
- ♦ 5µs Conversion Time
- ♦ On-Chip ±40ppm/°C Voltage Reference
- ♦ 90ns Access Time
- ◆ 215mW (Max) Power Consumption
- ♦ 24-Lead Narrow DIP and Wide SO Packages

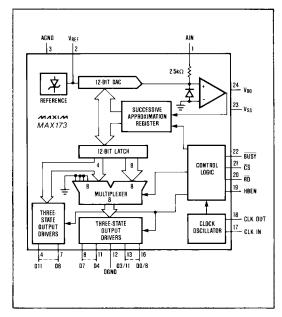
#### **Ordering Information**

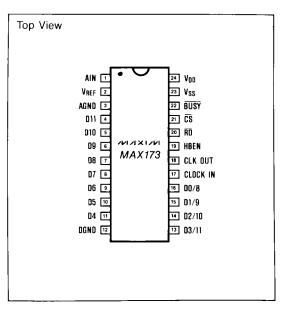
PART	TEMP. RANGE	PACKAGE*
MAX173CNG	0°C to +70°C	Plastic DIP
MAX173CWG	0°C to +70°C	Wide SO
MAX173C/D	0°C to +70°C	Dice**
MAX173ENG	-40°C to +85°C	Plastic DIP
MAX173EWG	-40°C to +85°C	Wide SO
MAX173MRG	-55°C to +125°C	CERDIP

- \* All devices 24 lead packages
- \*\* Consult factory for dice specifications.

#### Functional Diagram

### Pin Configurations





NINXIN

Maxim Integrated Products 1

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#### **ABSOLUTE MAXIMUM RATINGS**

$\begin{array}{cccccccccccccccccccccccccccccccccccc$	Operating Temperature Ranges 0°C to +70°C   MAX173XC 0°C to +85°C   MAX173XB -40°C to +85°C   MAX173XM -55°C to +125°C   Storage Temperature Range -65°C to +160°C   Power Dissipation (any Package) to +75°C 1000mW   Derates Above +75°C by 10mW/°C   Lead Temperature (Soldering 10 seconds) +300°C
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Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions above those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

#### **ELECTRICAL CHARACTERISTICS**

 $(V_{DD}$  = +5V  $\pm$  5%,  $V_{SS}$  = -12V or -15V  $\pm$  5%; Slow Memory Mode;  $T_A$  =  $T_{MIN}$  to  $T_{MAX}$  unless otherwise noted,  $f_{CLK}$  = 2.5MHz.)

PARAMETER	SYMBOL	CONDITIONS		MIN	TYP	MAX	UNITS
ACCURACY	•						
Resolution				12			Bits
No Missing Code Resolution				10			Bits
Integral Non-Linearity	INL				_	±0.05	%FSR
Offset Error (Note 1)						±5	mV
Full Scale Error (Note 2)						±0.4	%
Full Scale Tempco (Notes 3, 4)						±45_	ppm/°C
ANALOG INPUT							
Input Voltage Range				0		5	V
Input Current		AIN = 0V to +5V				3.5	mA
INTERNAL REFERENCE							
V <sub>REF</sub> Output Voltage		T <sub>A</sub> = 25°C		-5.2	-5.25	-5.3	V
V <sub>REF</sub> Output Tempco (Note 5)					±40		ppm/°C
Output Current Sink Capability		(Note 6)			_	5	mA
LOGIC INPUTS		-					
Input Low Voltage	VIL	CS, RD, HBEN, CLKIN				0.8	V
Input High Voltage	V <sub>IH</sub>	CS, RD, HBEN, CLKIN		2.4			V
Input Capacitance (Note 7)	Cin	CS RD, HBEN, CLKIN	CS RD, HBEN, CLKIN			10	pF
Input Current	I <sub>IN</sub>	CS, RD, HBEN CLKIN	VIN = 0 to V <sub>DD</sub>			±10 ±20	μΑ
LOGIC OUTPUTS							
Output Low Voltage	V <sub>OL</sub>	D11-D0/8, BUSY, CLKOUT ISINK = 1.6 mA				0.4	V
Output High Voltage	V <sub>OH</sub>	D11-D0/8, BUSY, CLKO	JT I <sub>SOURCE</sub> = 200μA	4			V
Floating State Leakage Current	ILKG	D11-D0/8, V <sub>OUT</sub> = 0V to	V <sub>DD</sub>			±10	μΑ
Floating State Output Capacitance (Note 7)	Соит					15	pF
CONVERSION TIME	-	•					
MAX173	t <sub>CONV</sub>	Synchronous (12.5 cloc Asynchronous (12 to 13		4.8		5 5.2	μs

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#### **ELECTRICAL CHARACTERISTICS (continued)**

 $(V_{DD} = +5V \pm 5\%, V_{SS} = -12V \text{ or } -15V \pm 5\%; \text{Slow Memory Mode; TA} = T_{MIN} \text{ to } T_{MAX} \text{ unless otherwise noted, } f_{CLK} = 2.5 \text{MHz.})$ 

PARAMETER	SYMBOL	CONDITIONS	MIN TYP MAX		MAX	UNITS
POWER SUPPLY REJECTION	ON			_		
V <sub>DD</sub> Only		FS Change, V <sub>SS</sub> = -15V, V <sub>DD</sub> = 4.75V to 5.25V	S Change, V <sub>SS</sub> = -15V, V <sub>DD</sub> = 4.75V to 5.25V			
V <sub>SS</sub> Only		FS Change, V <sub>DD</sub> = 5V, V <sub>SS</sub> = -5% to +5%	±0.01			%
POWER REQUIREMENTS						
V <sub>DD</sub>		$\pm$ 5% for Specified Performance 5				V
V <sub>SS</sub> (Note 8)		±5% for Specified Performance	ormance -12 or -15		5	V
I <sub>DD</sub>		CS = RD = V <sub>DD</sub> , AIN = 5V		5	7	mA
I <sub>SS</sub>		CS = RD = V <sub>DD</sub> , AIN = 5V	8 12		mA	
Power Dissipation		V <sub>DD</sub> = +5V, V <sub>SS</sub> = -15V	145 215		mW	

- **Note 1:** Typical change over temp is  $\pm 1.2$ mV.
- Note 2:  $V_{DD} = +5V$ ,  $V_{SS} = -15V$ , FS = +5.000V. Ideal last code transition = FS 1.8mV.
- **Note 3:** Full Scale TC =  $\Delta$ FS/ $\Delta$ T, where  $\Delta$ FS is full scale change from T<sub>A</sub> = 25°C to T<sub>MIN</sub> or T<sub>MAX</sub>.
- Note 4: Includes internal reference drift.
- Note 5:  $V_{REF}$  TC =  $\Delta V_{REF}/\Delta T$ , where  $\Delta V_{REF}$  is reference voltage change from  $T_A = 25^{\circ}$  C to  $T_{MIN}$  or  $T_{MAX}$ .
- Note 6: Output current should not change during conversion.
- Note 7: Guaranteed by design, not subject to test.
- Note 8: Functional operation at  $V_{SS} = -12V \pm 5\%$  is guaranteed by testing offset error and full scale error.

### TIMING CHARACTERISTICS (Note 9) (See MAX162 data sheet for t<sub>1</sub>-t<sub>10</sub> description)

 $(V_{DD} = +5V, V_{SS} = -12V \text{ or } -15V; T_A = T_{MIN} \text{ to } T_{MAX}, \text{ specifications in bold type are 100% tested, others are guaranteed by design, unless otherwise noted.)}$ 

PARAMETER	SYMBOL	CONDITIONS	T <sub>A</sub> = 25°C		MAX173C/E		MAX173M		UNITS	
			MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNITS
CS to RD Setup Time	t <sub>1</sub>		0			0		0		ns
RD to BUSY Delay (Note 12)	t <sub>2</sub>	C <sub>L</sub> = 50pF		90	190		230		270	ns
Data Access Time (Note 10)	t <sub>3</sub>	C <sub>L</sub> = 20pF		60	90		110		120	ns
Data Access Time (Notes 10, 12)	t <sub>3</sub>	C <sub>L</sub> = 100pF		70	125		150		170	ns
RD Pulse Width	t <sub>4</sub>		t <sub>3</sub>			t <sub>3</sub>		t <sub>3</sub>		
CS to RD Hold Time	t <sub>5</sub>		0			0		0		ns
Data Setup Time After BUSY (Notes 10, 12)	t <sub>6</sub>				80		105		120	ns
Bus Relinquish Time (Notes 11, 12)	t <sub>7</sub>				75		85		90	ns
HBEN to RD Setup Time	t <sub>8</sub>		0			0		0		ns
HBEN to RD Hold Time	t <sub>9</sub>		0			0		0		ns
Delay Between Read Operations	t <sub>10</sub>		200			200	·	200		ns

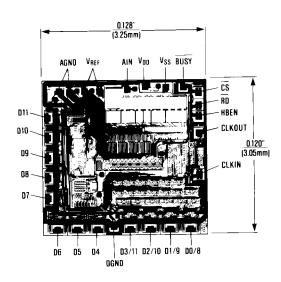
- Note 9: All input control signals are specified with t<sub>f</sub> = t<sub>r</sub> = 5ns (10% to 90% of +5V) and timed from a voltage level of +1.6V.
- Note 10: t<sub>3</sub> and t<sub>6</sub> are measured with the load circuits of Figure 1 (see MAX162 data sheet) and defined as the time required for an output to cross 0.8V or 2.4V
- Note 11: t<sub>7</sub> is defined as the time required for the data lines to change 0.5V when loaded with the circuits of Figure 2 (see MAX162 data sheet)
- Note 12: This specification is 100% production tested.

For additional information on using the MAX173 please refer to MAX162 data sheet.

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## Complete 5µs CMOS 10-Bit A/D Converter

### Chip Topography



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